

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

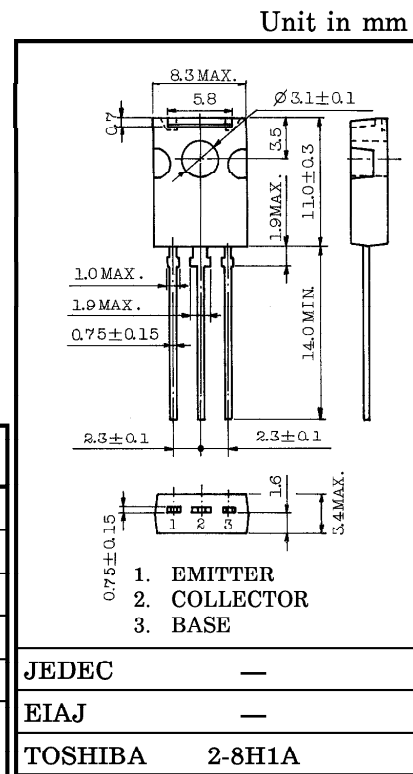
# 2SA1408

COLOR TV VERT. DEFLECTION OUTPUT APPLICATIONS.  
 COLOR TV CLASS B SOUND OUTPUT APPLICATIONS.

- Large Collector Current and Collector Power Dissipation Capability.
- Recommended for Vert. Deflection Output and Sound Output Applications for Line Operated TV.
- Complementary to 2SC3621.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V <sub>CB0</sub>	-150	V
Collector-Emitter Voltage		V <sub>CEO</sub>	-150	V
Emitter-Base Voltage		V <sub>EBO</sub>	-6	V
Collector Current		I <sub>C</sub>	-1.5	A
Base Current		I <sub>B</sub>	-0.3	A
Collector Power Dissipation	Ta = 25°C	P <sub>C</sub>	1.5	W
	Tc = 25°C		10	
Junction Temperature		T <sub>j</sub>	150	°C
Storage Temperature Range		T <sub>stg</sub>	-55~150	°C



Weight : 0.82g

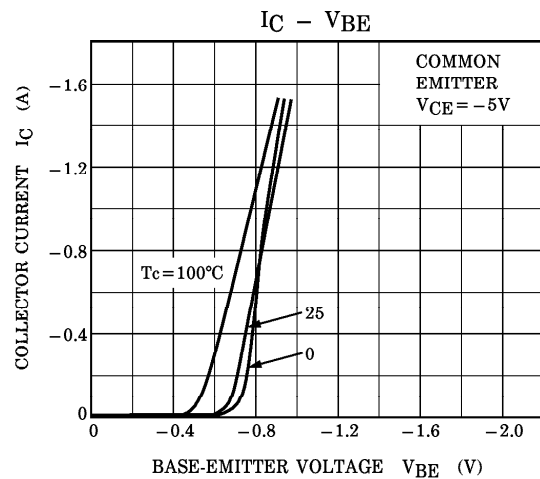
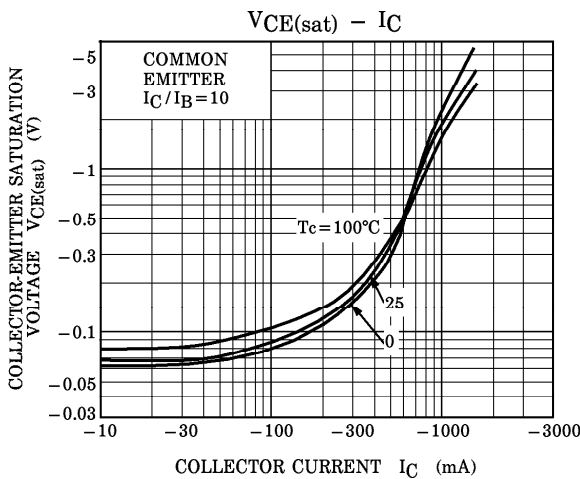
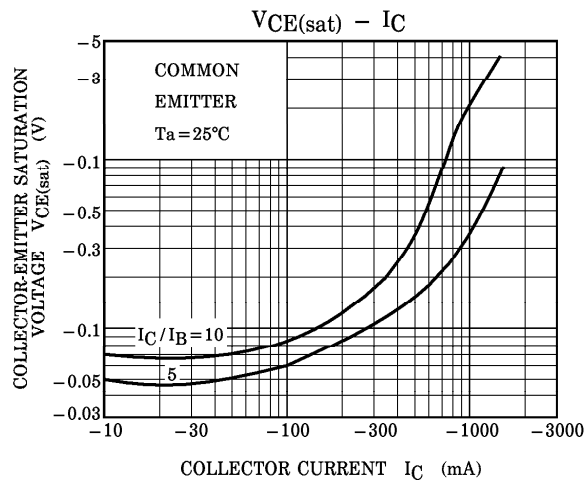
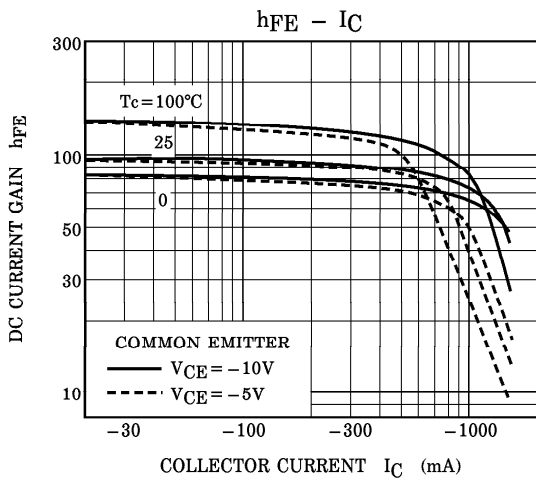
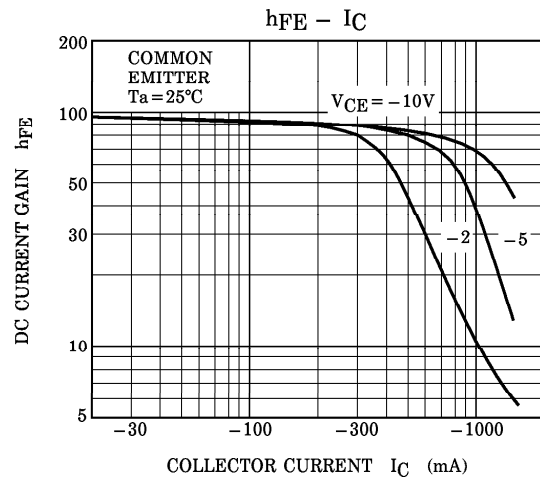
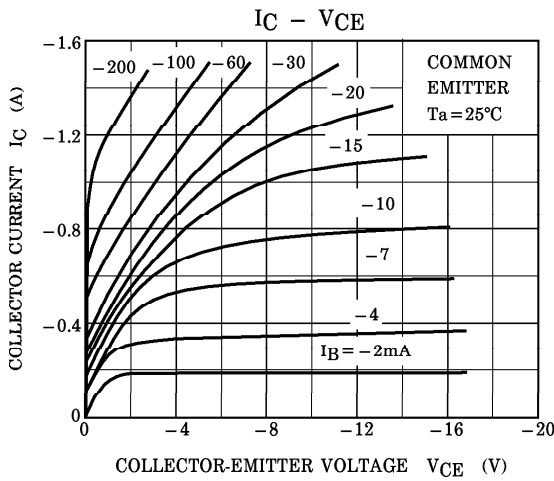
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I <sub>CB0</sub>	V <sub>CB</sub> = -150V, I <sub>E</sub> = 0	—	—	-1.0	μA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> = -6V, I <sub>C</sub> = 0	—	—	-1.0	μA
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -10mA, I <sub>B</sub> = 0	-150	—	—	V
DC Current Gain	h <sub>FE</sub> (Note)	V <sub>CE</sub> = -5V, I <sub>C</sub> = -200mA	60	—	200	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA	—	—	-1.5	V
Base-Emitter Voltage	V <sub>BE</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -5mA	-0.5	—	-0.8	V
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -200mA	15	50	—	MHz
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10V, I <sub>E</sub> = 0, f = 1MHz	—	—	35	pF

Note : h<sub>FE</sub> Classification R : 60~120 O : 100~200

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